

Mahatma Gandhi Mission's College of Engineering, Nanded Electronics and Telecommunication Engg. [202X-2X]

	Periodic Test I
Subject:	
Name of Course Instructor:	

Year: Fifth Year - B. Tech-ETC-A (Odd Sem)

Marks: 20 **Duration:** 60 Mins **Date:** DD/MM/YYYY

Note: All questions are COMPULSARY and carries EQUAL marks.

Figures to the right indicate full marks. Draw neat diagram wherever necessary.

Assume suitable data if necessary, stating it clearly.

Instructor

Sr. No.	Question	Marks	Course Outcome	Blooms Level	
1	All questions are COMPULSARY.				
1.1		5.00	CO_	BT	
1.2		5.00	CO_	BT	
1.3		5.00	CO_	BT	
1.4		5.00	CO_	BT	

Sample Copy of Periodic Test 1 (Internal) Marks distribution Scheme.

Mr/Ms/Mrs		Dr. K.P. Paithane
Name of Course	Module Coordinator	Head of Department



Mahatma Gandhi Mission's College of Engineering, Nanded

Electronics and Telecommunication Engg. [202X-2X]

	Periodic Test 2				
Subject	•				
Name o	f Course Instructor :				
Year/Se	em: (Odd/ Even Sem)				
Marks:	20 Date: DD/MM/YYYY			Duration: 6	0 Mins
Figures	Note: All questions are COMPULSARY and carries EQUAL marks. Figures to the right indicate full marks. Draw neat diagram wherever necessary. Assume suitable data if necessary, stating it clearly.				
Sr. No.	Question	Marks	Course Outcome	Blooms Level	
1	All questions are COMPULSARY.				
1.1		5.00	CO_	BT	
1.2		5.00	CO_	BT	
1.3		5.00	CO_	BT	
1.4		5.00	CO_	BT	
		<u> </u>			

Sample Copy of Periodic Test 2 (Internal) Marks distribution Scheme.

Mr/Ms/Mrs		Dr. K.P. Paithane
Name of Course	Module Coordinator	Head of Department

Instructor



MGM's College of Engineering, Nanded DEPARTMENT OF ELECTRONICS AND TELECOMMUNICATION ENGINEERING

CLASS: TY (ECT) SAMPLE MID SEM QUESTION PAPER

SUB: A.Y-202X-2X Sem-I Or II Date: DD/MM/YYYY Time: 60 Min

Sr.	Questions	Blooms	CO	Marks
No.	Questions	Taxonomy	No.	Wiaiks
Q.1	Attempt following questions:		1,00	6M
	1. MCQ Based Question			
	a.			
	b.	BT	CO_	
	c.			
	d.			
	2. MCQ Based Question			
	a.	DIE	00	
	b.	BT	CO_	
	c.			
	d.			
	3. MCQ Based Question			
	a. b.	BT	CO_	
	c.	D 1—		
	d.			
	4. MCQ Based Question			
	a.			
	b.	BT	CO_	
	c.			
	d.			
	5. MCQ Based Question			
	a.			
	b.	BT	CO_	
	c.			
	d.			
	6. MCQ Based Question			
	a.	DT	CO	
	b.	BT	CO_	
	C.			
0.1	d.			() (
Q.2	Attempt any two of the following questions:			6 M
	a)	BT	CO_	
	a)	BT	CO_	
	b)	BT	CO_	
0.2				0.74
Q.3	Attempt any one of the following questions:			8 M
	a)	BT	CO_	
		1	•	I .

Sample Copy of Mid Sem Exa	am (External) Marks distribu	ition Scheme.
Name of Course Instructor	Module Coordinator	Dr. K.P. Paithane Prof. & Head of Dept.

	DR. BABASAHEB Regula	r & Supplementai			•		
	Course: B. Tech.	Branch : E	•			Semester :IV	
	Subject Code & Nam						
	Max Marks: 60	Date:2	6/07/2023		Duration	n: 3 Hr.	
	which the quest 3. Use of non-pro		ntioned in () fic calculator	in front of s is allowe	the question. d.	, ,	
						(Level/CO)	Ma
Q. 1	Solve Any Two of the	e following.					
A)	received as '0' is 0.95 0.9. if probability that 1) A '1' is received	For a certain binary communication channel probability that transmitted '0' received as '0' is 0.95 and probability that transmitted '1' received as '1' is 0.9. if probability that '0' transmitted is 0.4. Find the probability that 1) A '1' is received 2) A '1' is transmitted given that '1' was received.				L2/CO1	
B)	State and explain Theo			state Bayes	'Theorem.	L1/C01	
C)	From 6 positive and 8					L2/CO1	
	(without replacement).	. What is the probab	oility that pro	duct is pos	sitive.		
Q.2	Solve Any Two of the	e following.					
A)	What are PDF and CD	F. State and explain	n properties o	of CDF		L1/CO2	
B)	Suppose the density fu F(x,y)=6xy(2-x-y) 0 < 0 = O otherwise Compute condition	'	·	=y where (0 <y<1.< td=""><td>L2/CO2</td><td></td></y<1.<>	L2/CO2	
	Calculate the correlation	on coefficient betwe	een X& Y fro	om followi	ng data	L2/CO2	
C)	X 10	14 18	22	26	30		
C)	10			20	36		
C)	Y 18	12 24	6	30	30		
	Y 18		6	30	30		
Q. 3	Y 18 Solve Any Two of the	e following.	6	30	30	L1/CO3	
Q. 3 A)	Y 18 Solve Any Two of the State and prove Tcheb	e following. ycheff Inequality.				L1/C03	
Q. 3	Y 18 Solve Any Two of the	e following. ycheff Inequality. fic stop at 15 min it 7.30, 7.45 and so oniformly distributed	nterval starti	ng from 7 <i>a</i> ger arrives	AM. That is at a stop at	L1/CO3 L2/CO3	

	b) At least 12 mins for the bus		
C)	State and Explain properties of Covariance matrix	L1/CO3	6
Q.4	Solve Any Two of the following.		12
A)	Explain in detail with proof central limit theorem	L1/CO4	6
B)	Distinguish between WLLN and SLLN in detail.	L1/CO4	6
C)	How to determine convergence in Probability. Elaborate in brief	L1/CO4	6
Q. 5	Solve Any Two of the following.		12
A)	A random process is given by	L2/CO5	6
	$X(t) = A \cos w_0 t + B \sin w_0 t$		
	Where w ₀ is constant . A& B are independent random variables having val-		
	ues -1 and 2 with probabilities 2/3 and 1/3 respectively. Find mean and auto-		
	correlation function.		
B)	Explain in brief Strict Sense Stationary process (SSS) and Wide Sense	L1/CO5	6
	Stationary (SSS) Process		
C)	Explain power spectral density function with its properties.	L1/CO5	6
	*** End ***		

DR. BABASAHEB AMBEDKAR TECHNOLOGICAL UNIVERSITY, LONERE

Supplementary Summer Examination – 2023

Course: B. Tech. Branch: E&TC Engineering Semester: VI

Subject Code & Name: BTETPE604A CMOS Design

Max Marks: 60 Date: 26/07/2023 Duration: 2:00 to 5:00 PM

Instructions to the Students:

- 1. All the questions are compulsory.
- 2. The level of question/expected answer as per OBE or the Course Outcome (CO) on which the question is based is mentioned in () in front of the question.
- 3. Use of non-programmable scientific calculators is allowed.
- 4. Assume suitable data wherever necessary and mention it clearly.

	4. Assume suitable data wherever necessary and mention it clearly.		•
		(Level/CO)	Marks
Q. 1	Solve Any Two of the following.		12
A)	Explain various steps involved in CMOS inverter n-well fabrication	3/1	6
B)	Draw Schematic, stick diagram and layout for 2 input CMOS AND gate	3/2	6
	With equal rise and fall times		
C)	Draw Voltage transfer characteristics for static CMOS Inverter. And	1/1	6
	explain working of inverter.		
Q.2	Solve Any Two of the following.		12
A)	Draw the schematic and layout for two input CMOS NOR gate, Use	2/1	6
	CMOS Lambda based design rules.		
B)	Explain Subthreshold leakage the non-ideal effect in MOSFET	1/1	6
C)	Explain leakage power in CMOS inverter. What are ways to reduce it?	1/1	6
Q. 3	Solve Any Two of the following.		12
A)	Implement AND/NAND gate using CMOS dual rail domino logic	3/2	6
B)	Explain Set up, hold time & propagation delay for a sequential circuit	1/1	6
	in detail		
C)	Draw Truth Table, Gate level diagram and then implement JK Flip-	3/2	6
	Flop using static CMOS design style.		
Q.4	Solve Any Two of the following.		12
A)	Write a short note on CMOS scaling	2/1	6
B)	Implement half adder combinational circuit using static CMOS logic.	2/2	6
C)	Explain Channel Length Modulation (CLM) non-ideal effect in	1/1	6
	MOSFET		

Q. 5	Solve Any Two of the following.		12
A)	Explain MOSFET parasitic capacitances in detail	1/1	6
B)	Explain Body effect on threshold voltage of the MOSFET	1/1	6
C)	Implement $Y = \overline{ABC}$ using dynamic CMOS design style.	3/2	6

*** End ***